

L Number	Hits	Search Text	DB	Time stamp
-	1	("5319229").PN.	USPAT; US-PGPUB	2002/10/31 18:32
-	14	5319229.URPN.	USPAT	2002/10/31 18:22
-	83	("gate dielectric" SAME ("high K" or "high dielectric") same (oxide or SiO or "SiO.sub.2" or dioxide)) and ((nitrogen with (implant or implanting or implanted) or nitrida\$ or nitriding or nitritating or nitriding or nitrided))	USPAT; US-PGPUB	2002/11/01 09:38
-	16	("3668004" "3730766" "3967310" "4335391" "4495219" "4636833" "4659606" "4690846" "4891684" "4937650" "4989056" "5072269" "5091761" "5111355" "5173835" "5225286").PN.	USPAT	2002/10/31 18:58
-	4	((("high k" or "high dielectric") WITH (oxide or nitride or dioxide or oxynitride)) SAME (anneal\$) SAME (silicate)	USPAT; US-PGPUB	2002/10/31 19:23
-	38	("gate insulator" SAME ("high K" or "high dielectric" or "metal oxide") same (oxide or SiO or "SiO.sub.2" or dioxide)) and ((nitrogen with (implant or implanting or implanted) or nitrida\$ or nitriding or nitritating or nitriding or nitrided or nitridification))	USPAT; US-PGPUB	2002/11/01 09:40
-	1109	(anneal\$ or RTP or RTA) SAME ("metal oxide" or "hafnium oxide" or HfO or "zirconium oxide" or "ZrO.sub.2" or "tantalum oxide" or "titanium dioxide" or "TiO.sub.2" or "cesium oxide" or "lantanum" or "tungsten oxide" or yttrium or BSO or BST or BSrO or PZN or PZT or PST) SAME (dioxide or "silicon oxide" or SiO or "SiO.sub.2" or oxynitride or SiON or SiN or "nitride")	USPAT; US-PGPUB	2002/11/01 11:46
-	231	((anneal\$ or RTP or RTA) SAME ("metal oxide" or "hafnium oxide" or HfO or "zirconium oxide" or "ZrO.sub.2" or "tantalum oxide" or "titanium dioxide" or "TiO.sub.2" or "cesium oxide" or "lantanum" or "tungsten oxide" or yttrium or BSO or BST or BSrO or PZN or PZT or PST) SAME (dioxide or "silicon oxide" or SiO or "SiO.sub.2" or oxynitride or SiON or SiN or "nitride")) and (silicate)	USPAT; US-PGPUB	2002/11/01 10:27
-	36	((anneal\$ or RTP or RTA) SAME ("metal oxide" or "hafnium oxide" or HfO or "zirconium oxide" or "ZrO.sub.2" or "tantalum oxide" or "titanium dioxide" or "TiO.sub.2" or "cesium oxide" or "lantanum" or "tungsten oxide" or yttrium or BSO or BST or BSrO or PZN or PZT or PST) SAME (dioxide or "silicon oxide" or SiO or "SiO.sub.2" or oxynitride or SiON or SiN or "nitride")) SAME silicate	USPAT; US-PGPUB	2002/11/01 10:27
-	357	(438/287).CCLS.	USPAT; US-PGPUB	2002/11/01 10:51
-	271	(438/217).CCLS.	USPAT; US-PGPUB	2002/11/01 10:57
-	1477	((composite or alternate or alternating) WITH (insulator or dielectric or insulating)) SAME gate	USPAT; US-PGPUB	2002/11/01 11:01
-	213	((composite or alternate or alternating) WITH (insulator or dielectric or insulating)) SAME gate) and ("high k" or "higher k" or "higher dielectric" or "high dielectric")	USPAT; US-PGPUB	2002/11/01 11:11

-	32	((((composite or alternate or alternating) WITH (insulator or dielectric or insulating)) SAME gate) and ("high k" or "higher k" or "higher dielectric" or "high dielectric")) and silicate	USPAT; US-PGPUB	2002/11/01 11:46
-	1270	("metal oxide" or "hafnium oxide" or HfO or "zirconium oxide" or "ZrO.sub.2" or "tantalum oxide" or "Ta.sub.2 O.sub.5" or "titanium dioxide" or "TiO.sub.2" or "cesium oxide" or "lantanum" or "tungsten oxide" or yttrium or BSO or BST or BSrO or PZN or PZT or PST) WITH (reacting or reacted or react or reaction) WITH (silicate or silicon)	USPAT; US-PGPUB	2002/11/01 12:38
-	150	((("metal oxide" or "hafnium oxide" or HfO or "zirconium oxide" or "ZrO.sub.2" or "tantalum oxide" or "Ta.sub.2 O.sub.5" or "titanium dioxide" or "TiO.sub.2" or "cesium oxide" or "lantanum" or "tungsten oxide" or yttrium or BSO or BST or BSrO or PZN or PZT or PST) WITH (reacting or reacted or react or reaction) WITH (silicate or silicon)) and gate	USPAT; US-PGPUB	2002/11/01 12:39
-	5	("5441906" "5668024" "5691225" "5780362" "5807770").PN.	USPAT	2002/11/01 13:09
-	4	5904517.URPN.	USPAT	2002/11/01 13:10